

DB101 THRU DB107

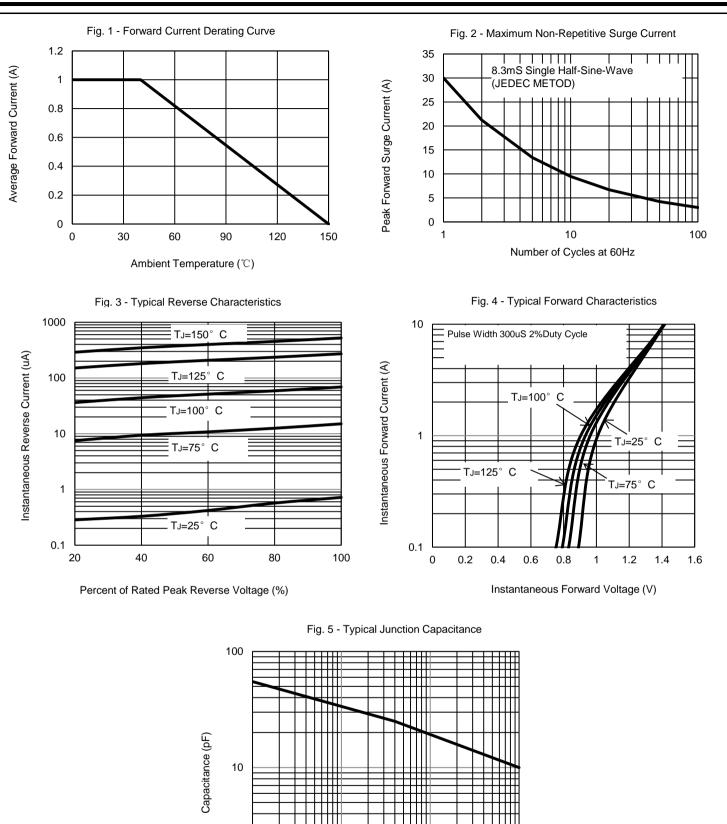
Glass Passivated Bridge Rectifiers		Reverse Voltage - 50 to 1000 Volts							
		Forward Current - 1.0 Amperes							
									Rb
Features		DB							
Glass passivated chip			-			.335(Delle
 High surge forward current capability Reliable low cost construction utilizing 			<u></u>	<u>- (1</u> + 1)-	-	.307((.4)	c	RoHS
molded plastic technique			_			ίλ.	— hi		
 Lead tin plated copper 					256(6.5) 244(6.2)		(
 Meet UL flammability classification 94V-0 			~	<u>~ </u>	•		N.		
Mechanical Data			IJ	U		Ű 	ן איז בא		
Polarity: Symbol marked on body			. 3460	8,7),		300(
Mounting position: Any									
		.022(0.5	o. ÌÍ —)í	193(4			1	
Applications		.018(0.44	ŕΨ		<u> +</u>			•	
 General purpose use in AC/DC bridge full wave rectification 	tion,		= .205(= .195(5.U) =1	(1.5)				
for SMPS, lighting ballaster, adapter, etc.			SPAC	ING					
	Package Outline Dimensions in Inches (Millimeters)								
Maximum Ratings and Electrical Charact	eristic	S							
Rating at 25 $^\circ\!\mathrm{C}$ ambient temperature unless otherwise spe	cified.								
Single phase, half wave, 60Hz, resistive or inductive load.									
For capacitive load, derate current by 20%.									
Characteristics	Symbol	DB101	DB102	DB103	DB104	DB105	DB106	DB107	Unit
Maximum Repetitive Peak Reverse Voltage	Vrrm	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	VRMS	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	VDC	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @Ta=40 $^\circ\!\mathrm{C}$	I(AV)	1.0						А	
Peak Forward Surge Current, 8.3mS Single Half Sine-Wave,	IFSM		30						٨
Superimposed on Rated Load (JEDEC Method)	IFSM	30							A
I ² t Rating for Fusing (t<8.3mS)	l ² t	3.7						A ² s	
Peak Forward Voltage per Diode at 1.0A DC	VF	1.1						V	
Maximum DC Reverse Current at Rated @Tj=25 $^\circ$ C	lr	10							μA
DC Blocking Voltage per Diode @Tj=125°C	ік	500							
Typical Junction Capacitance (Note1)	Сл	25						pF	
Typical Thermal Resistance Junction to Ambient (Note2)	Reja	40						°C/W	
Operating Junction Temperature Range	TJ	-55 to +150						°C	
Storage Temperature Range	Tstg	-55 to +150						°C	
Notes: 1. Measured at 1.0 MUT and applied reverse valtage of 1.									

Notes: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0V DC.

2. Thermal resistance from junction to ambient mounted on P.C.B ,with 0.5*0.5"(13*13mm) copper pads.

3. The typical data above is for reference only .

Rating and Characteristic Curves DB101 THRU DB107



TJ=25° C,f=1MHz

1

Reverse Voltage (V)

10

100

1 └ 0.1

The curve above is for reference only.